



SamHop Microelectronics Corp.



STU664S

STD664S

Ver 1.0

N-Channel Logic Level Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

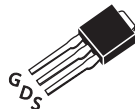
V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
60V	30A	20 @V _{GS} =10V

FEATURES

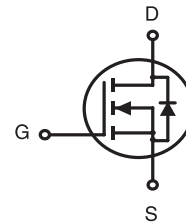
- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-252 and TO-251 Package.



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V _{DS}	Drain-Source Voltage		60	V
V _{GS}	Gate-Source Voltage		±20	V
I _D	Drain Current-Continuous ^a	T _C =25°C	30	A
		T _C =70°C	24	A
I _{DM}	-Pulsed ^a		88	A
E _{AS}	Single Pulse Avalanche Energy ^c		100	mJ
P _D	Maximum Power Dissipation	T _C =25°C	42	W
		T _C =70°C	27	W
T _J , T _{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case	3	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	50	°C/W

Details are subject to change without notice.

Jun,05,2013

STU664S

STD664S

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V , V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V , V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	2.6	4	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V , I _D =15A		16	20	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V , I _D =15A		22		S
DYNAMIC CHARACTERISTICS ^b						
C _{iss}	Input Capacitance	V _{DS} =25V,V _{GS} =0V f=1.0MHz		2190		pF
C _{oss}	Output Capacitance			140		pF
C _{rss}	Reverse Transfer Capacitance			105		pF
SWITCHING CHARACTERISTICS ^b						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =30V I _D =1A V _{GS} =10V R _{GEN} = 6 ohm		47		ns
t _r	Rise Time			31		ns
t _{D(OFF)}	Turn-Off Delay Time			62		ns
t _f	Fall Time			13		ns
Q _g	Total Gate Charge	V _{DS} =30V,I _D =15A,V _{GS} =10V		36		nC
Q _{gs}	Gate-Source Charge	V _{DS} =30V,I _D =15A, V _{GS} =10V		6		nC
Q _{gd}	Gate-Drain Charge			12		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V,I _S =6A		0.81	1.3	V
Notes						
a.Drain current limited by maximum junction temperatrue.						
b.Guaranteed by design, not subject to production testing.						
c.Starting T _J =25°C,L=0.5mH,V _{DD} = 30V.(See Figure13)						

Jun,05,2013

STU664S STD664S

Ver 1.0

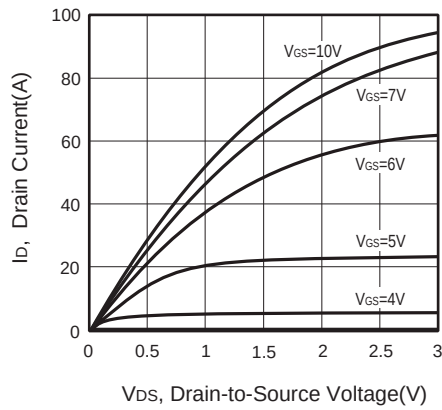


Figure 1. Output Characteristics

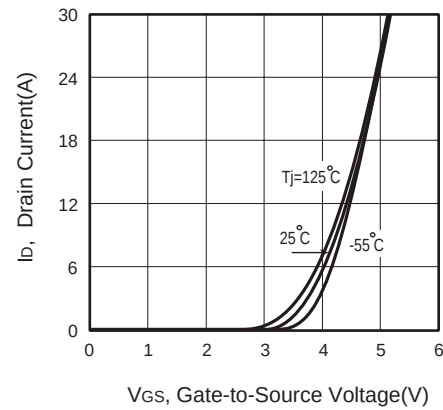


Figure 2. Transfer Characteristics

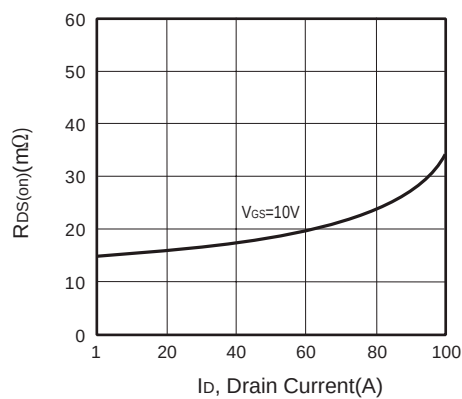


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

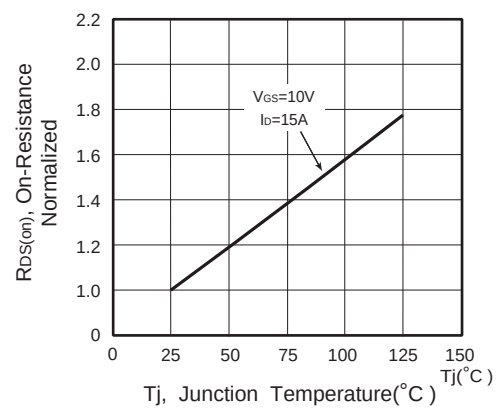


Figure 4. On-Resistance Variation with Drain Current and Temperature

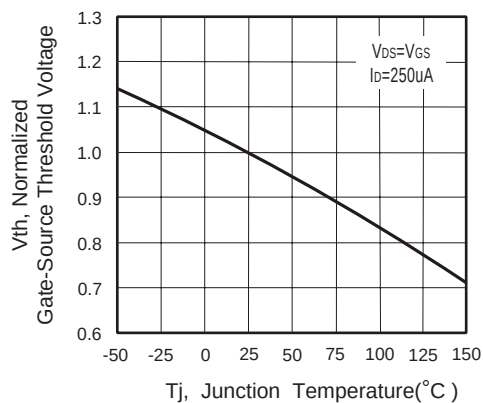


Figure 5. Gate Threshold Variation with Temperature

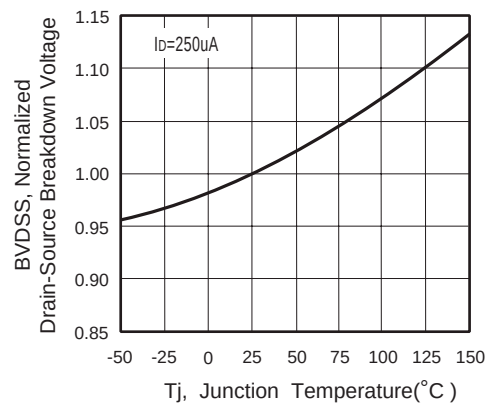


Figure 6. Breakdown Voltage Variation with Temperature

Jun,05,2013

STU664S STD664S

Ver 1.0

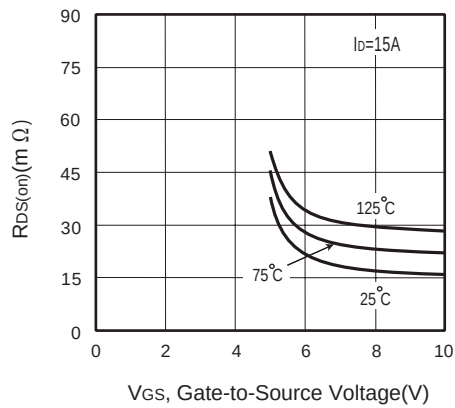


Figure 7. On-Resistance vs. Gate-Source Voltage

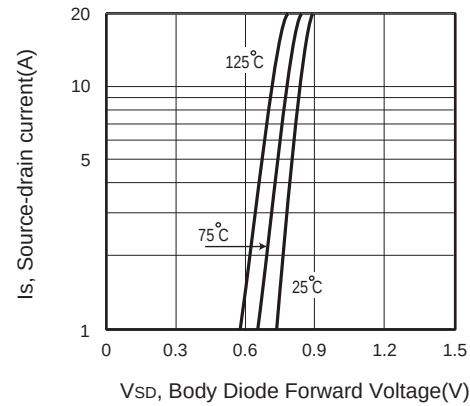


Figure 8. Body Diode Forward Voltage Variation with Source Current

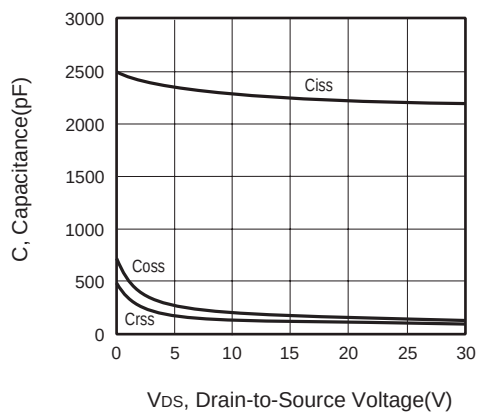


Figure 9. Capacitance

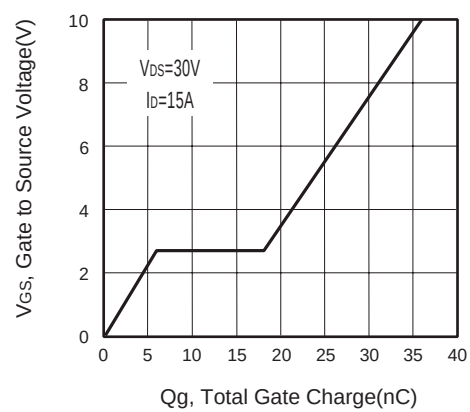


Figure 10. Gate Charge

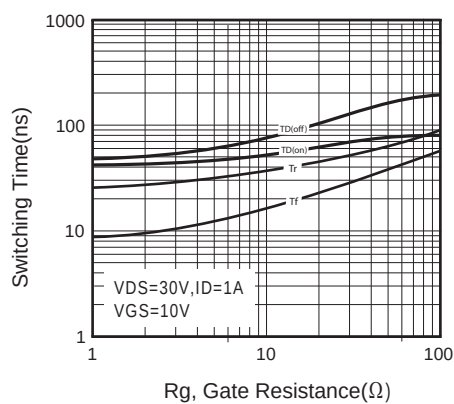


Figure 11. switching characteristics

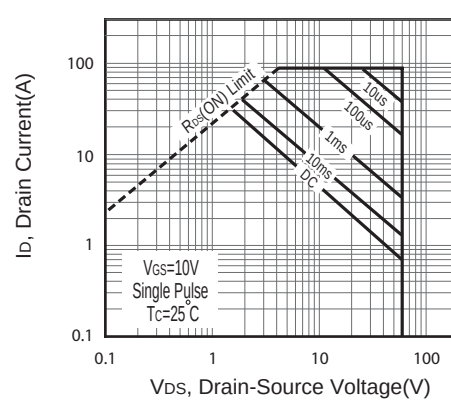
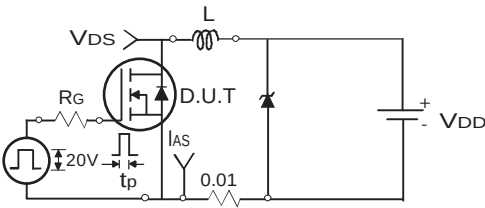


Figure 12. Maximum Safe Operating Area

Jun,05,2013

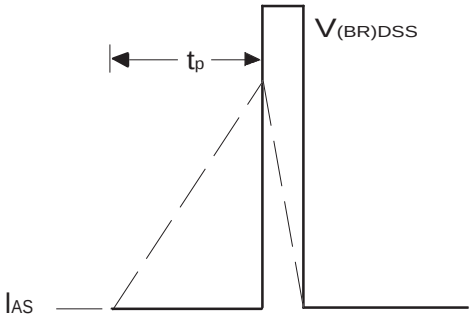
STU664S
STD664S

Ver 1.0



Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

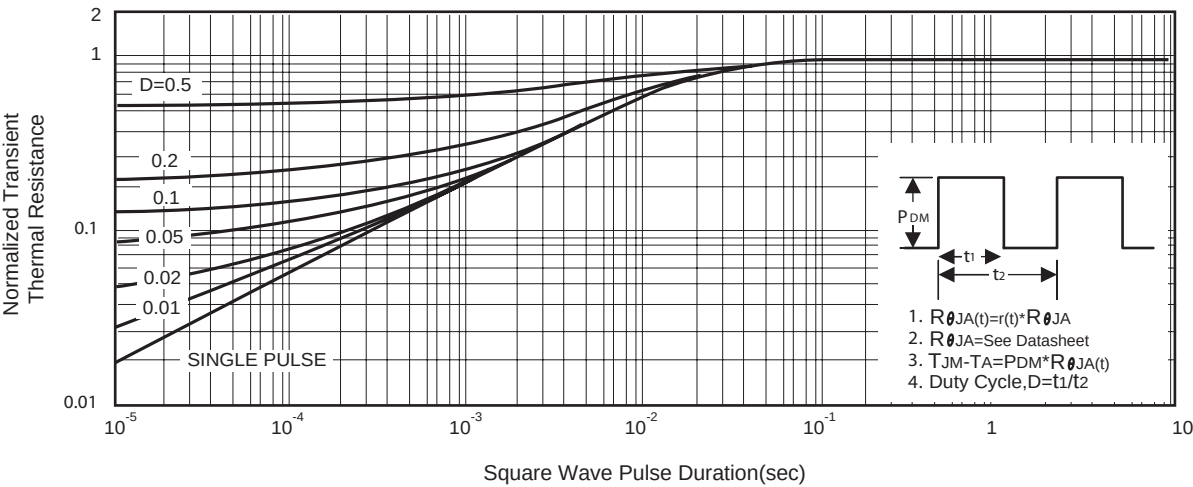


Figure 14. Normalized Thermal Transient Impedance Curve

Jun,05,2013

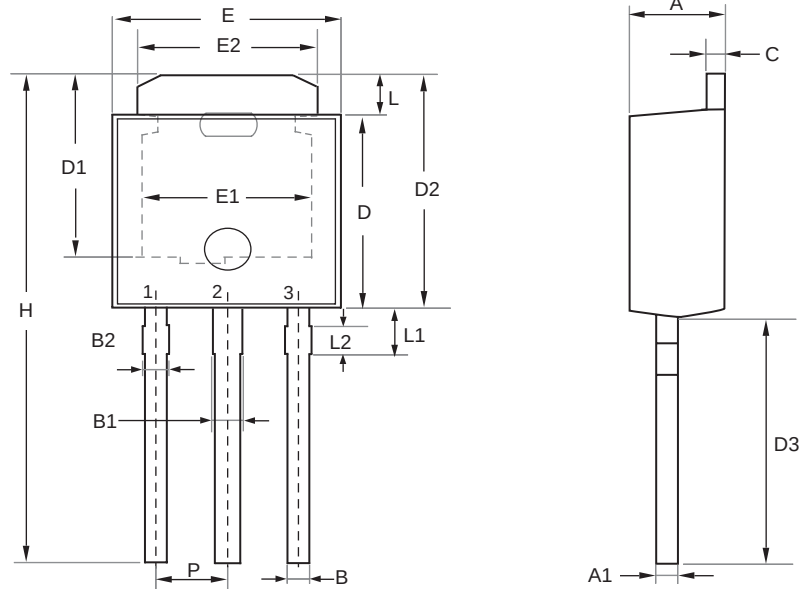
STU664S

STD664S

Ver 1.0

PACKAGE OUTLINE DIMENSIONS

TO-251



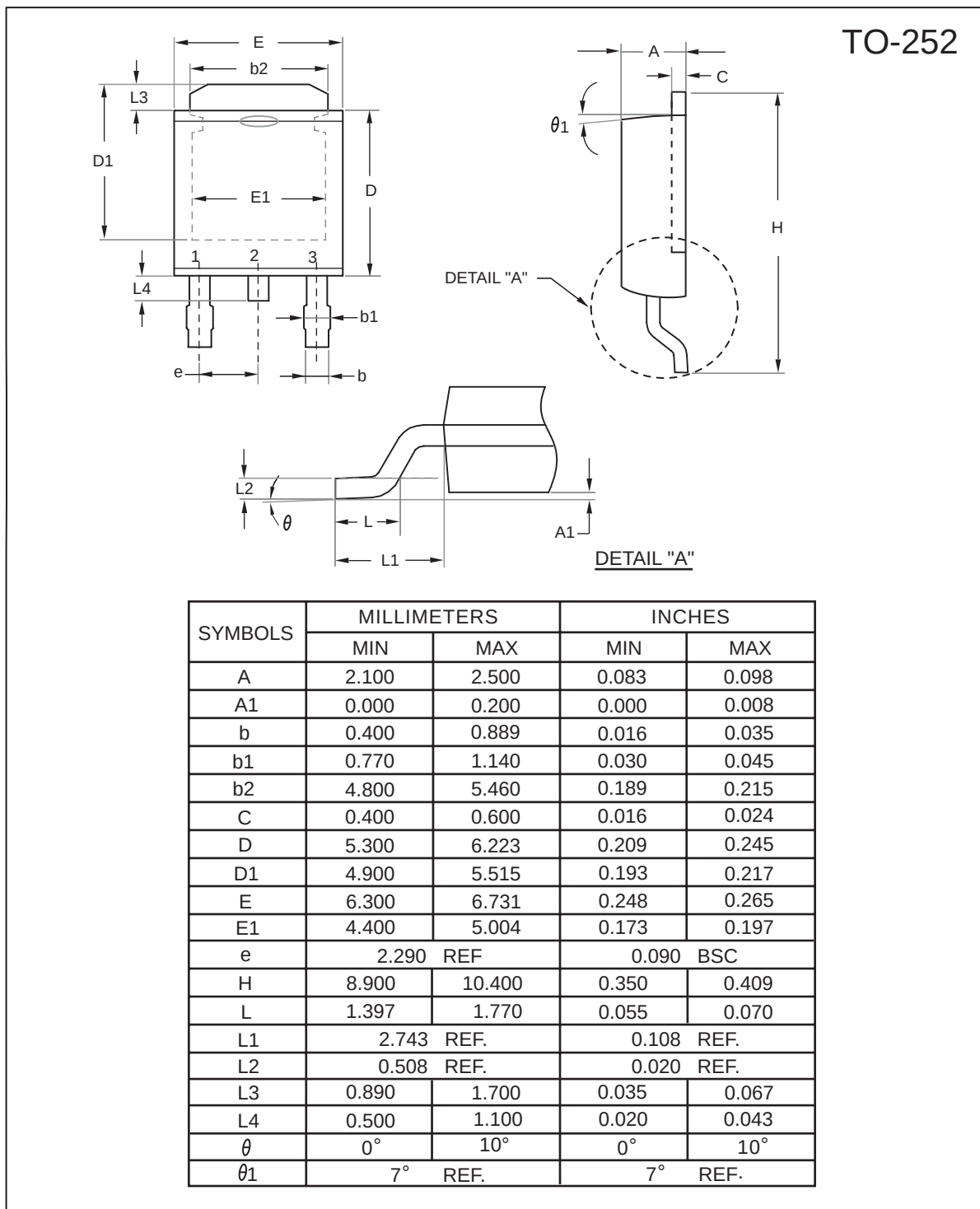
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.350	0.650	0.014	0.026
B	0.400	0.800	0.016	0.031
B1	0.650	1.050	0.026	0.041
B2	0.500	0.900	0.020	0.035
C	0.400	0.600	0.016	0.024
D	5.300	5.700	0.209	0.224
D1	4.900	5.300	0.193	0.209
D2	6.700	7.300	0.264	0.287
D3	7.000	8.000	0.276	0.315
H	10.830	11.430	0.426	0.450
E	6.300	6.700	0.248	0.264
E1	4.600	4.900	0.181	0.193
E2	4.800	5.200	0.189	0.205
L	1.300	1.700	0.051	0.067
L1	1.400	1.800	0.055	0.071
L2	0.500	0.900	0.020	0.035
P	2.300 BSC		0.091 BSC	

Jun,05,2013

STU664S

STD664S

Ver 1.0



Jun,05,2013

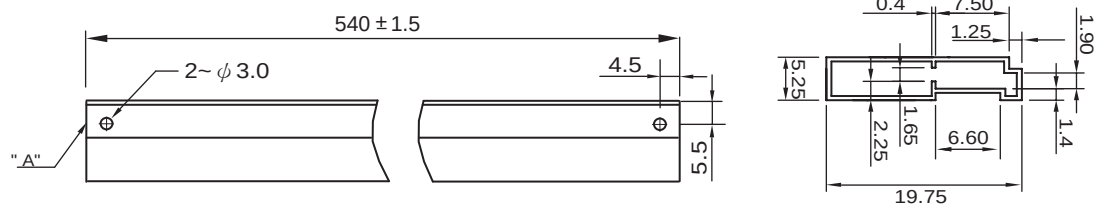
STU664S

STD664S

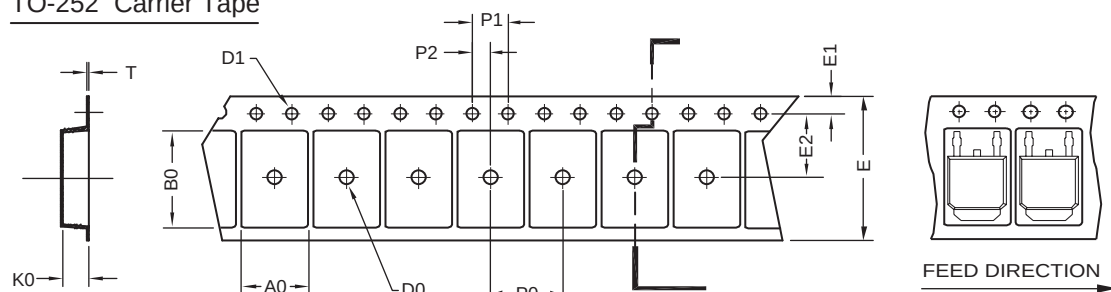
Ver 1.0

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



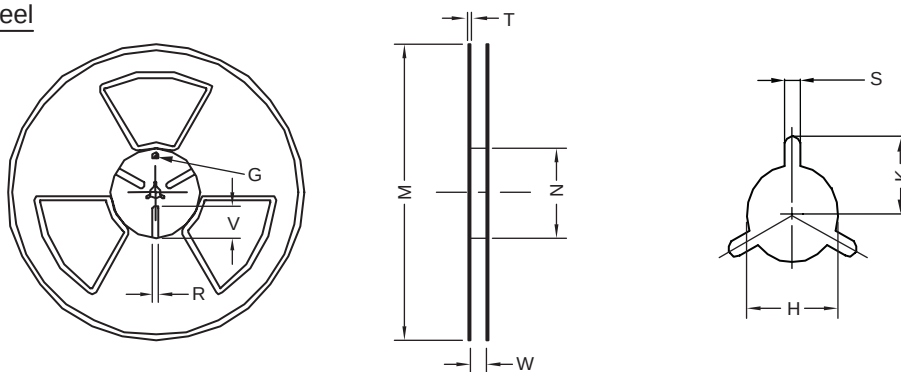
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 +0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---

Jun,05,2013